Q. Metrology, Inspection, and Yield Enhancement 분과

Room H
1F / 110호

2015년 2월 12일(목) 13:10-14:40
[TH3-Q] Metrology, Inspection, and Yield Enhancement
좌장: 김호섭 (선문대학교), 유형원 (SK하이닉스)

TH3-Q-1	**14:50-15:05**	**Thermoreflectance Microscopy and Applications for Thermal Characterization of Semiconductor Devices** Ki Soo Chang, Dong Uk Kim, Seon Young Ryu, and Woo June Choi Center for Analytic Instrumentation Development, Korea Basic Science Institute
TH3-Q-2	**15:05-15:20**	**Quantifying Precision Limit for Multichannel Spectroscopic Ellipsometers** Yong Jai Cho, Won Chegal, Jeong Pyo Lee, and Hyun Mo Cho Division of Industrial Metrology, Korea Research Institute of Standards and Science
TH3-Q-3	**15:20-15:35**	**2D-Strain Measurement in Transistor by Scanning Moiré Fringe Imaging** Younheum Jung, Suhyun Kim, Joong Jung Kim, Sunyoung Lee, and Haebum Lee Memory Analysis Science & Engineering Group, Samsung Electronics
TH3-Q-4	**15:35-15:50**	**XPS를 이용한 Atomic Layer Deposition된 Hafnium Oxide 박막과 Aluminum Oxide 박막의 전자 구조 측정** JongSung Han, Junghan Lee, SungHo Lee, Taeyoung Ra, Sangik Lee, Changhyuk Ok, Sunyoung Lee, and Haebum Lee Department of Device analysis group, Samsung Electronics
TH3-Q-5	**15:50-16:05**	**고분해능 TEM 과 암시야 전자홀로그래피를 이용한 InxGa1-x N MQWs 내 In 조성 및 격자변형의 정량적 분석** 조영지 [1,2], 양준모 [1], 박경진 [1], 유정호 [1], 장지호 [2] [1]나노종합기술원 특성평가실, [2]한국해양대학교 응용과학과
TH3-Q-6	**16:05-16:20**	**2D Strain Measurement in Sub-10 nm SiGe Layer with Dark-Field Electron Holography** Van Vuong Hoang[1,2], Young Ji Cho[1], Jung Ho Yoo[1], Soon-Ku Hong[2], Yong Ho Choi[3], and Jun-Mo Yang[1] [1]Department of Measurement & Analysis, National Nanofab Center, [2]Department of Materials Science and Engineering, Chungnam National University, [3]Department of High-Tech Materials Engineering, Jungwon University